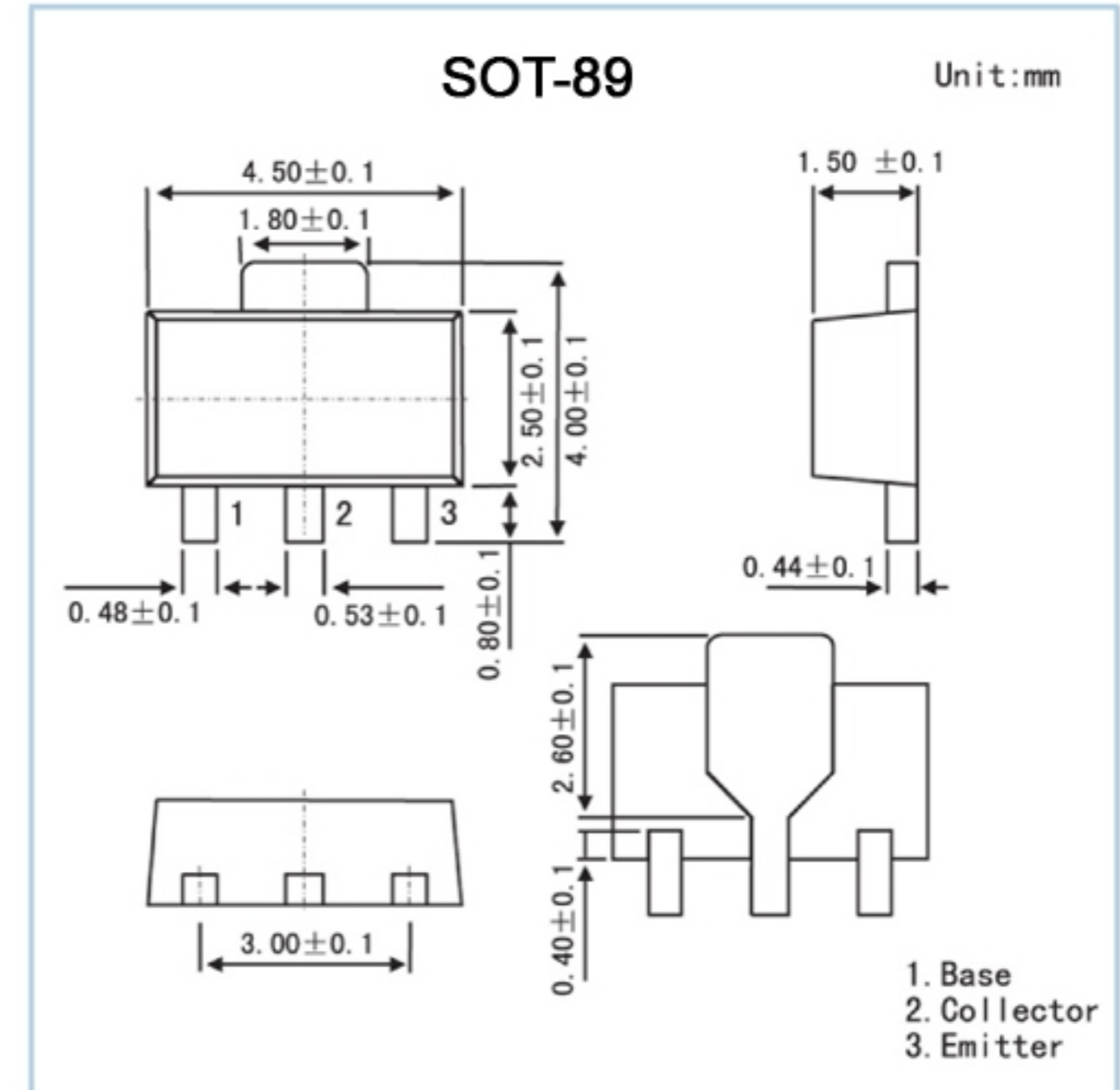


■ Features

- Suitable For Output Stage of 3 Watts Amplifier
- Small Flat Package
- $P_c = 1$ to 2W (mounted on ceramic substrate)
- Complementary to 2SC2883



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	-30	V
Collector-Emitter Voltage	V_{CE0}	-30	V
Emitter-Base Voltage	V_{EB0}	-5	V
Collector Current	I_c	-1.5	A
Base Current	I_B	-0.3	A
Collector Power Dissipation	P_c	500	mW
	P_{c^*}	1000	
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$

* Mounted on ceramic substrate ($250\text{ mm}^2 \times 0.8\text{ t}$)

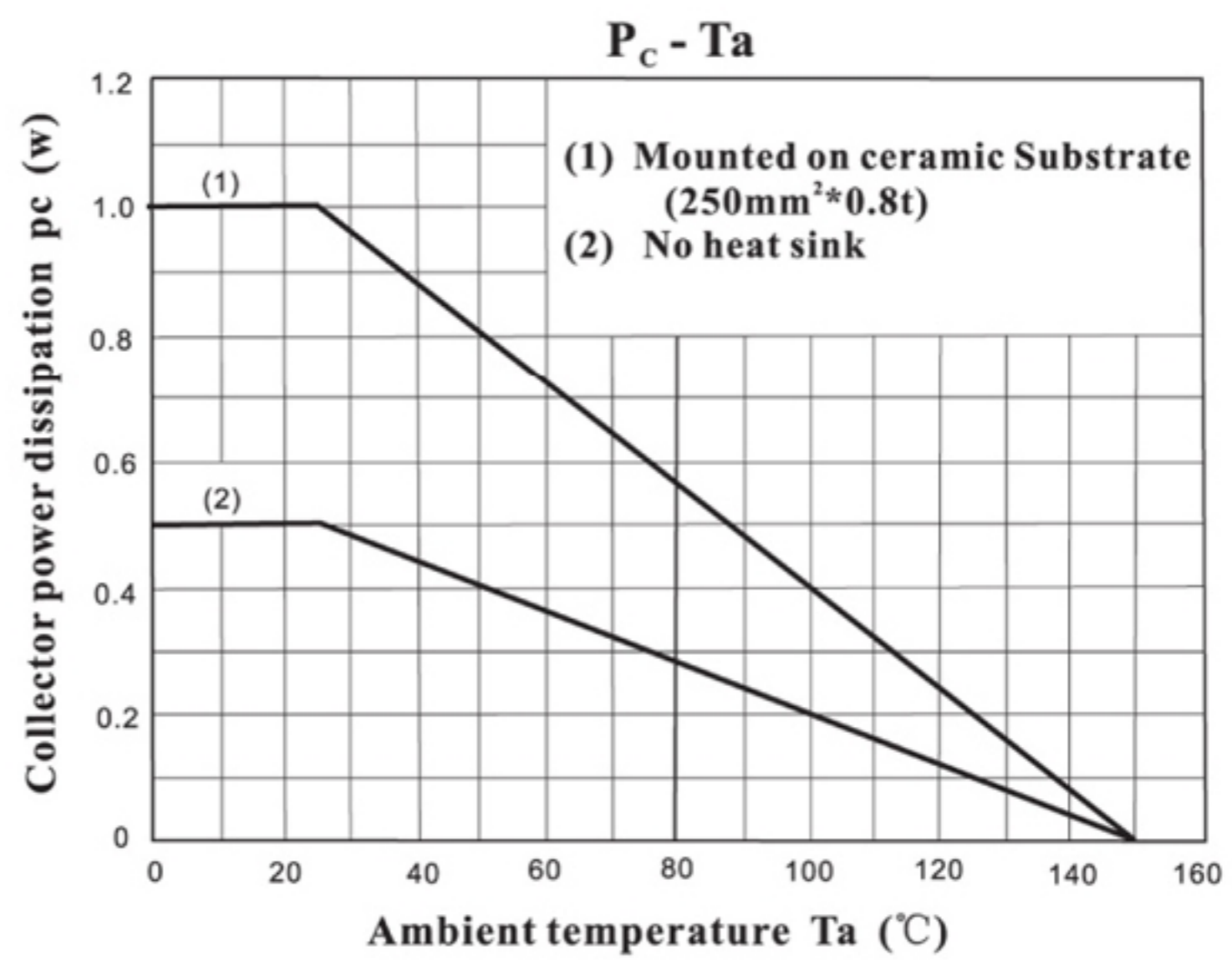
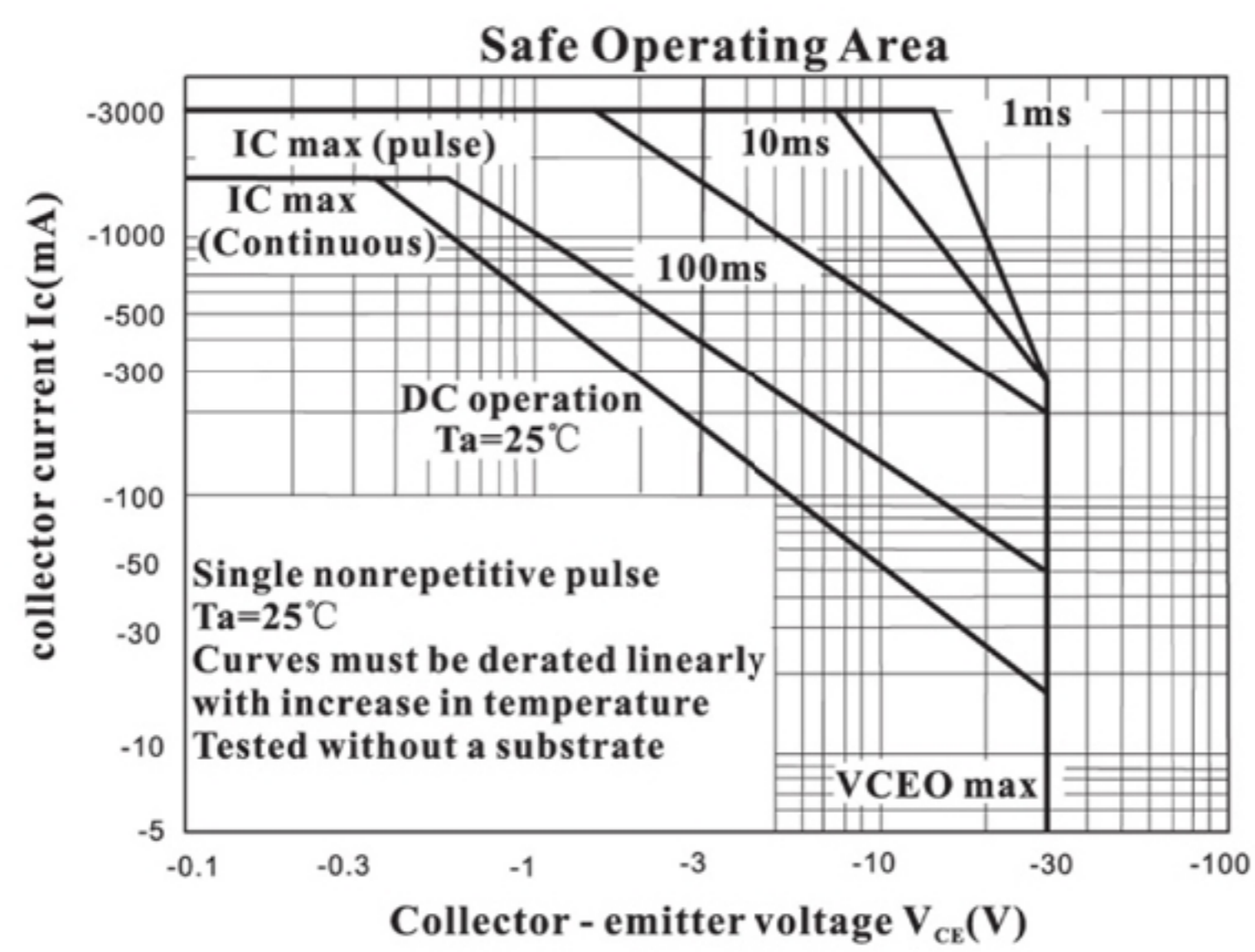
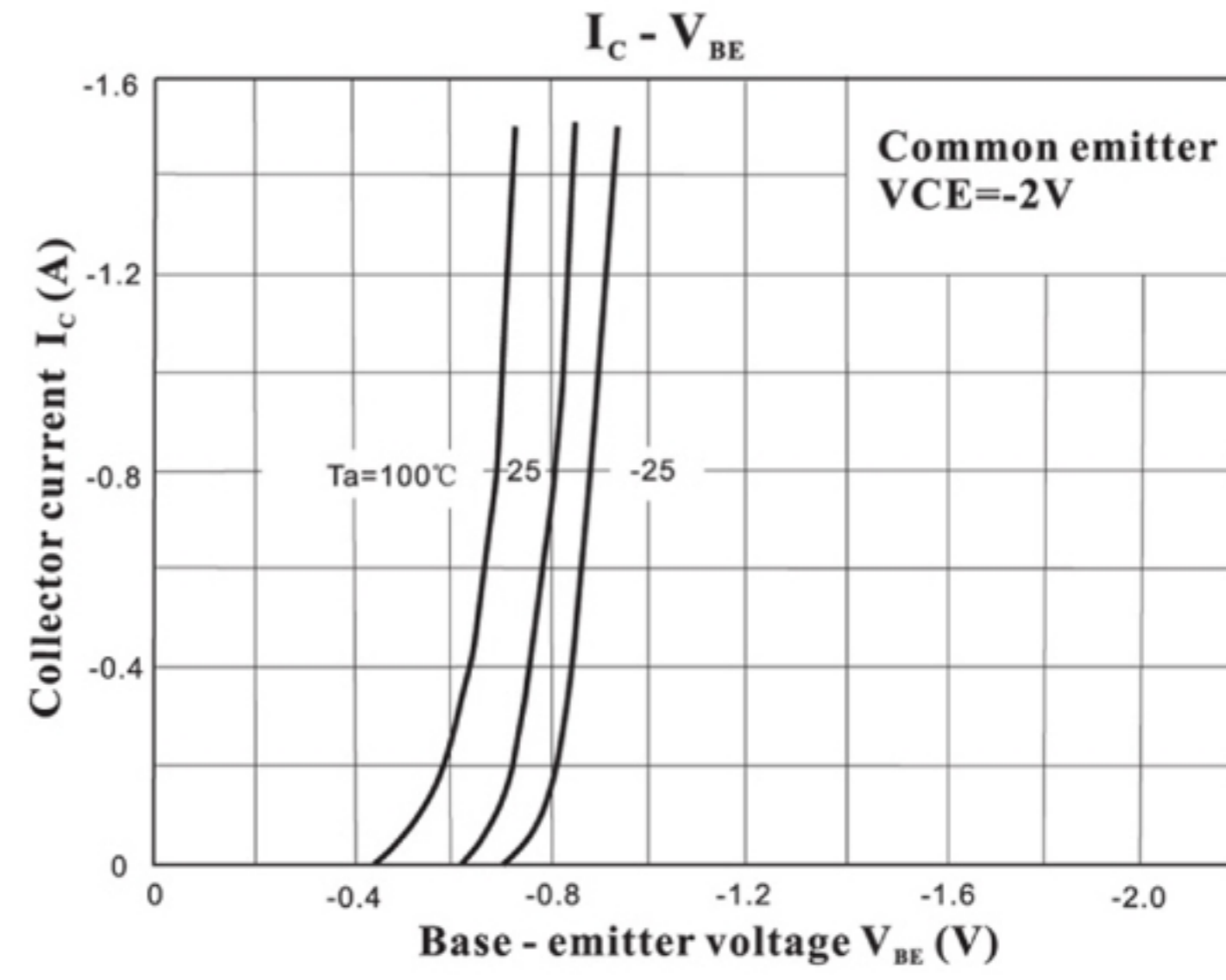
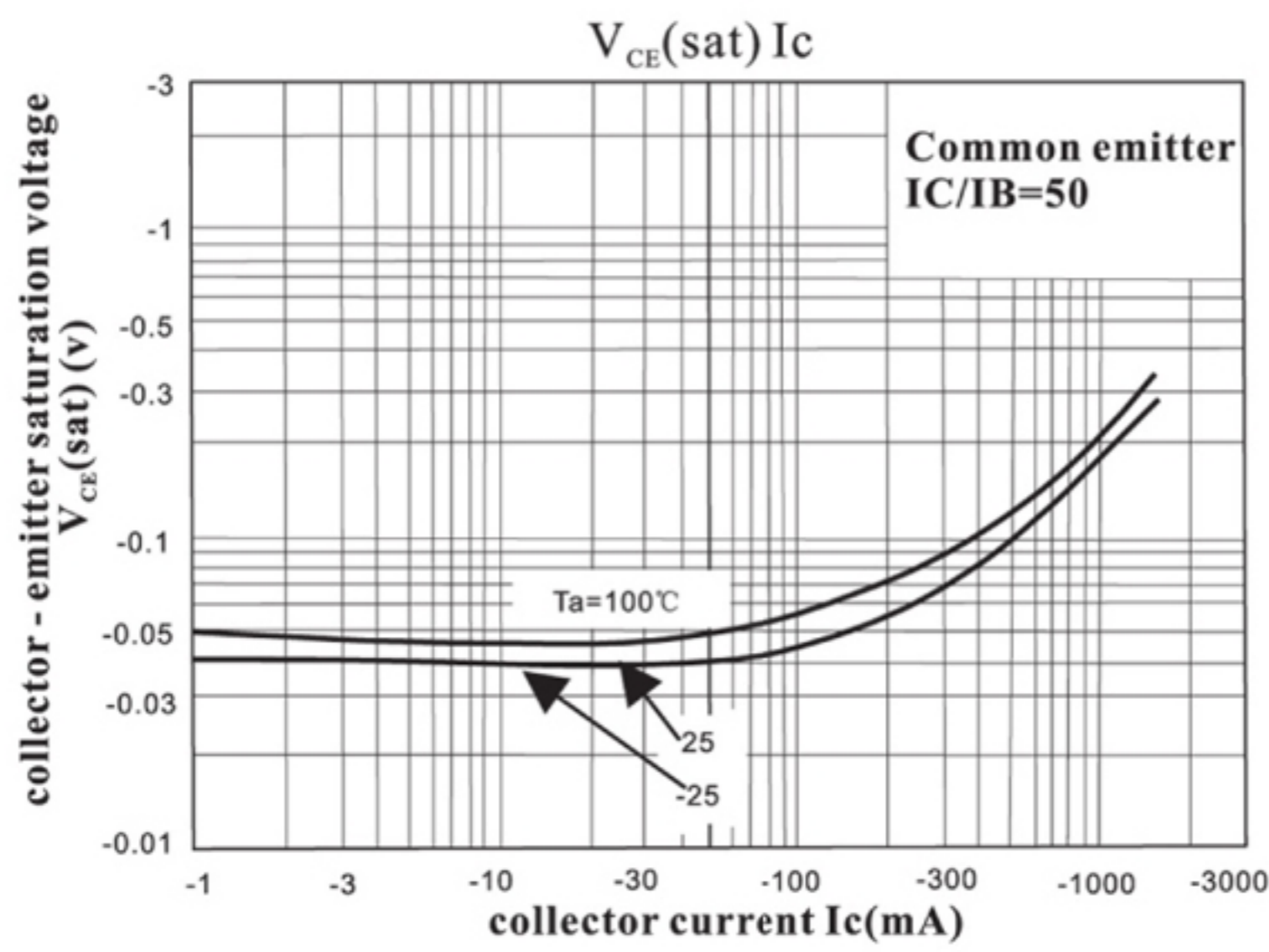
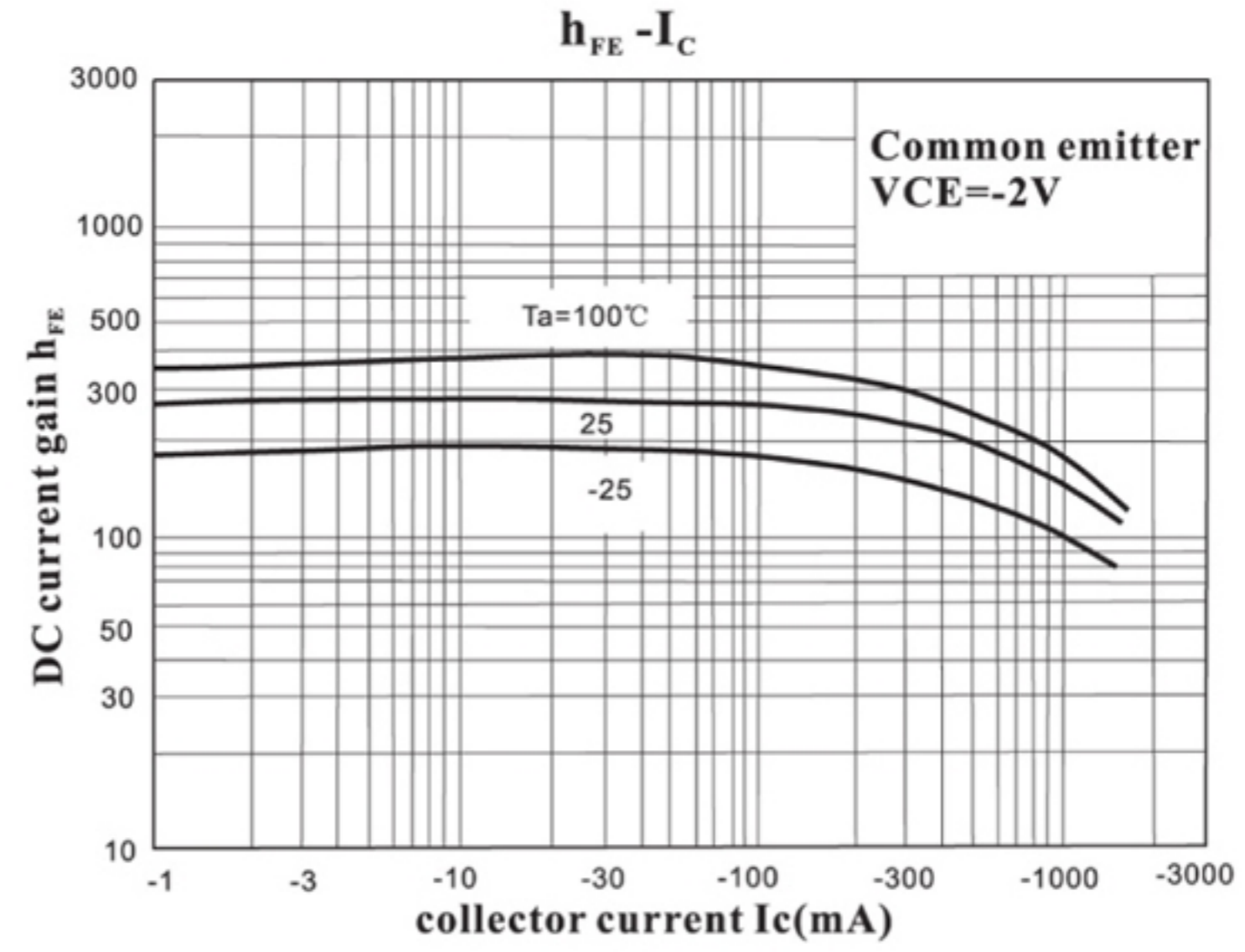
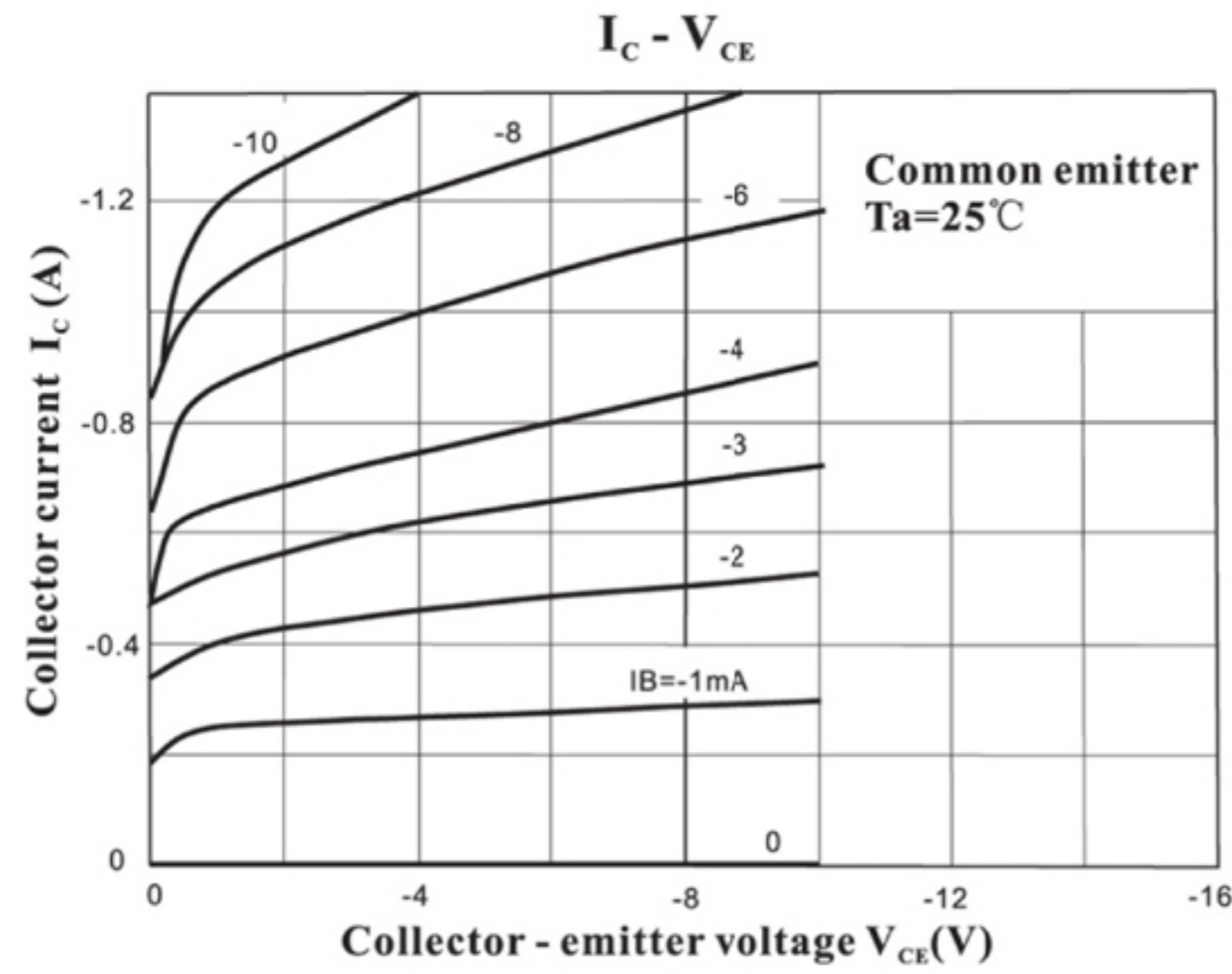
■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector Cut-off Current	I_{CB0}	$V_{CB} = -30\text{V}, I_E = 0$			-0.1	μA
Emitter Cut-off Current	I_{EB0}	$V_{EB} = -5\text{V}, I_C = 0$			-0.1	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10\text{mA}, I_B = 0$	-30			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -1\text{mA}, I_C = 0$	-5			V
DC Current Gain	h_{FE}	$V_{CE} = -2\text{V}, I_C = -500\text{mA}$	100		320	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -1.5\text{A}, I_B = -0.03\text{A}$			-2.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -2\text{V}, I_C = -500\text{mA}$			-1.0	V
Transition Frequency	f_T	$V_{CE} = -2\text{V}, I_C = -500\text{mA}$		120		MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$			50	pF

hFE Classification

Marking	H	
Rank	O	Y
hFE	100 ~ 200	160 ~ 320

Electrical Characteristics Curves



单击下面可查看定价，库存，交付和生命周期等信息

[>>SHIKUES\(时科\)](#)